

Product Overview

NGTB30N120FL2: IGBT, 1200V 30A FS2 Solar/UPS

For complete documentation, see the data sheet.

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop II Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. The IGBT is well suited for UPS and solar applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

Features

- Extremely Efficient Trench with Field Stop Technology
- $T_{Jmax} = 175^{\circ}C$
- Soft Fast Reverse Recovery Diode
- Optimized for High Speed Switching
- 10 μ s Short Circuit Capability

Applications

- Solar Inverter
- Uninterruptible Power Supplies (UPS)
- Welding

Part Electrical Specifications

| Product | Compliance | Status | $V_{ES}^{(BR)C}$ Typ (V) | I_C Max (A) | $V_{GE}^{(sa)}$ Typ (V) | V_F Typ (V) | E_{off} Typ (mJ) | E_{on} Typ (mJ) | T_{rr} Typ (ns) | I_{rr} Typ (A) | Gate Charge Typ (nC) | Short Circuit With stand (μ s) | E_{AS} Typ (mJ) | P_D Max (W) | Co- Pack aged Diode | Pack age Type |
|-----------------|------------------------|--------|--------------------------------|---------------------|-------------------------------|---------------------|--------------------------|-------------------------|-------------------------|------------------------|-------------------------------|---|-------------------------|---------------------|------------------------------|---------------------|
| NGTB30N120FL2WG | Pb-free Halide free | Active | 1200 | 30 | 2 | 1.75 | 0.7 | 2.6 | 240 | 18 | 220 | 10 | - | 452 | Yes | TO-247-3 |

For more information please contact your local sales support at www.onsemi.com.

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